

# **Excellent Integrated System Limited**

Stocking Distributor

Click to view price, real time Inventory, Delivery & Lifecycle Information:

ON Semiconductor NSBA143TDXV6T1G

For any questions, you can email us directly: sales@integrated-circuit.com



## MUN5116DW1, NSBA143TDXV6

# Dual PNP Bias Resistor Transistors R1 = 4.7 kΩ, R2 = $\infty$ kΩ

# PNP Transistors with Monolithic Bias Resistor Network

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

#### **Features**

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### **MAXIMUM RATINGS**

(T<sub>A</sub> = 25°C, common for Q<sub>1</sub> and Q<sub>2</sub>, unless otherwise noted)

Rating	Symbol	Max	Unit
Collector-Base Voltage	V <sub>CBO</sub>	50	Vdc
Collector-Emitter Voltage	$V_{CEO}$	50	Vdc
Collector Current - Continuous	Ic	100	mAdc
Input Forward Voltage	V <sub>IN(fwd)</sub>	30	Vdc
Input Reverse Voltage	V <sub>IN(rev)</sub>	5	Vdc

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MUN5116DW1T1G, SMUN5116DW1T1G	SOT-363	3,000/Tape & Reel
NSBA143TDXV6T1G	SOT-563	4,000/Tape & Reel
NSBA143TDXV6T5G	SOT-563	8,000/Tape & Reel

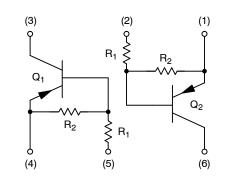
<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



#### ON Semiconductor®

http://onsemi.com

#### **PIN CONNECTIONS**



#### **MARKING DIAGRAMS**



SOT-363 CASE 419B





SOT-563 CASE 463A



0F = Specific Device Code

M = Date Code\*
■ Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation may vary depending upon manufacturing location.

## **Distributor of ON Semiconductor: Excellent Integrated System Limited**

Datasheet of NSBA143TDXV6T1G - TRANS 2PNP PREBIAS 0.5W SOT563 Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com

#### MUN5116DW1, NSBA143TDXV6

#### THERMAL CHARACTERISTICS

Characteristic		Symbol	Max	Unit
MUN5116DW1 (SOT-363) ONE JUNCTION HEATED				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 1) (Note 2) (Note 1) (Note 2)	P <sub>D</sub>	187 256 1.5 2.0	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ hetaJA}$	670 490	°C/W
MUN5116DW1 (SOT-363) BOTH JUNCTION HEATED (Note 3)				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 1) (Note 2) (Note 1) (Note 2)	$P_D$	250 385 2.0 3.0	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ hetaJA}$	493 325	°C/W
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{ hetaJL}$	188 208	°C/W
Junction and Storage Temperature Range		$T_J$ , $T_{stg}$	-55 to +150	°C
NSBA143TDXV6 (SOT-563) ONE JUNCTION HEATED				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 1) (Note 1)	$P_{D}$	357 2.9	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1)	$R_{ hetaJA}$	350	°C/W
NSBA143TDXV6 (SOT-563) BOTH JUNCTION HEATED (Note 3	3)			
Total Device Dissipation  T <sub>A</sub> = 25°C  Derate above 25°C	(Note 1) (Note 1)	P <sub>D</sub>	500 4.0	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1)	$R_{ hetaJA}$	250	°C/W
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

- FR-4 @ Minimum Pad.
   FR-4 @ 1.0 x 1.0 Inch Pad.
   Both junction heated values assume total power is sum of two equally powered channels.

#### MUN5116DW1, NSBA143TDXV6

#### ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C, common for Q<sub>1</sub> and Q<sub>2</sub>, unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	<u> </u>				
Collector-Base Cutoff Current $(V_{CB} = 50 \text{ V}, I_E = 0)$	I <sub>CBO</sub>	-	-	100	nAdc
Collector-Emitter Cutoff Current $(V_{CE} = 50 \text{ V}, I_B = 0)$	I <sub>CEO</sub>	-	-	500	nAdc
Emitter-Base Cutoff Current $(V_{EB} = 6.0 \text{ V}, I_C = 0)$	I <sub>EBO</sub>	-	-	1.9	mAdc
Collector-Base Breakdown Voltage (I <sub>C</sub> = 10 μA, I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	50	-	-	Vdc
Collector-Emitter Breakdown Voltage (Note 4) $(I_C = 2.0 \text{ mA}, I_B = 0)$	V <sub>(BR)CEO</sub>	50	-	-	Vdc
ON CHARACTERISTICS					
DC Current Gain (Note 4) (I <sub>C</sub> = 5.0 mA, V <sub>CE</sub> = 10 V)	h <sub>FE</sub>	160	250	-	
Collector-Emitter Saturation Voltage (Note 4) $(I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA})$	V <sub>CE(sat)</sub>	-	-	0.25	V
Input Voltage (Off) ( $V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}$ )	V <sub>i(off)</sub>	-	0.58	-	Vdc
Input Voltage (On) (V <sub>CE</sub> = 0.2 V, I <sub>C</sub> = 10 mA)	V <sub>i(on)</sub>	-	1.0	-	Vdc
Output Voltage (On) $(V_{CC} = 5.0 \text{ V}, V_B = 2.5 \text{ V}, R_L = 1.0 \text{ k}\Omega)$	V <sub>OL</sub>	-	-	0.2	Vdc
Output Voltage (Off) ( $V_{CC} = 5.0 \text{ V}, V_B = 0.25 \text{ V}, R_L = 1.0 \text{ k}\Omega$ )	V <sub>OH</sub>	4.9	-	-	Vdc
Input Resistor	R1	3.3	4.7	6.1	kΩ
Resistor Ratio	R <sub>1</sub> /R <sub>2</sub>	_	_	-	

<sup>4.</sup> Pulsed Condition: Pulse Width = 300 ms, Duty Cycle ≤ 2%.

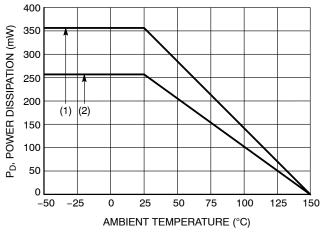


Figure 1. Derating Curve

- (1) SOT-363;  $1.0\times1.0$  Inch Pad
- (2) SOT-563; Minimum Pad



#### MUN5116DW1, NSBA143TDXV6

#### TYPICAL CHARACTERISTICS MUN5116DW1, NSBA143TDXV6

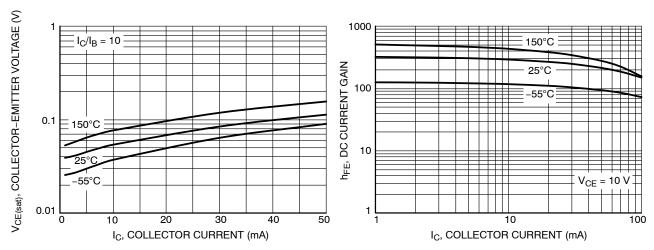


Figure 2. V<sub>CE(sat)</sub> vs. I<sub>C</sub>

Figure 3. DC Current Gain

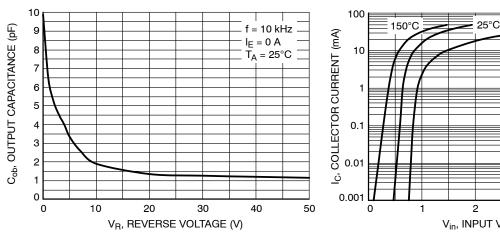


Figure 4. Output Capacitance

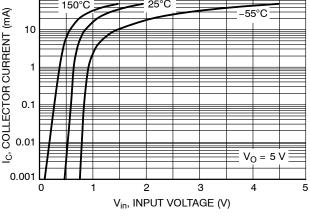


Figure 5. Output Current vs. Input Voltage

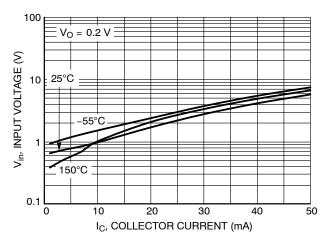


Figure 6. Input Voltage vs. Output Current

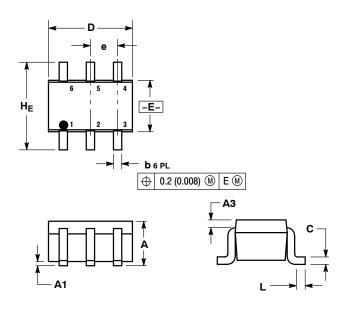
#### **Distributor of ON Semiconductor: Excellent Integrated System Limited**

Datasheet of NSBA143TDXV6T1G - TRANS 2PNP PREBIAS 0.5W SOT563 Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com

#### MUN5116DW1, NSBA143TDXV6

#### **PACKAGE DIMENSIONS**

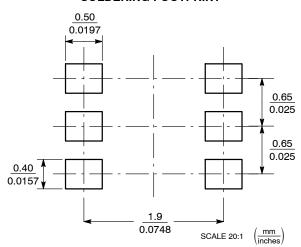
SC-88/SC70-6/SOT-363 CASE 419B-02 ISSUE W



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. 419B-01 OBSOLETE, NEW STANDARD 419B-02.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.80	0.95	1.10	0.031	0.037	0.043
A1	0.00	0.05	0.10	0.000	0.002	0.004
А3	0.20 REF			0.008 REF		
b	0.10	0.21	0.30	0.004	0.008	0.012
С	0.10	0.14	0.25	0.004	0.005	0.010
D	1.80	2.00	2.20	0.070	0.078	0.086
E	1.15	1.25	1.35	0.045	0.049	0.053
е	0.65 BSC			0	.026 BS	С
L	0.10	0.20	0.30	0.004	0.008	0.012
He	2 00	2 10	2 20	0.078	0.082	0.086

#### **SOLDERING FOOTPRINT\***



#### SC-88/SC70-6/SOT-363

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## Distributor of ON Semiconductor: Excellent Integrated System Limited

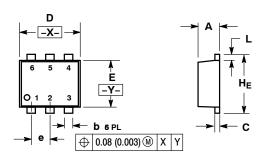
Datasheet of NSBA143TDXV6T1G - TRANS 2PNP PREBIAS 0.5W SOT563

Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com

#### MUN5116DW1, NSBA143TDXV6

#### PACKAGE DIMENSIONS

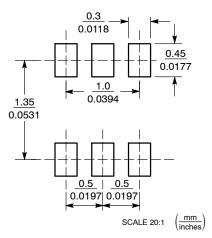
SOT-563, 6 LEAD CASE 463A **ISSUE F** 



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982.
  CONTROLLING DIMENSION: MILLIMETERS
  MAXIMUM LEAD THICKNESS INCLUDES LEAD
  FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.50	0.55	0.60	0.020	0.021	0.023
b	0.17	0.22	0.27	0.007	0.009	0.011
С	0.08	0.12	0.18	0.003	0.005	0.007
D	1.50	1.60	1.70	0.059	0.062	0.066
Е	1.10	1.20	1.30	0.043	0.047	0.051
е	0.5 BSC				0.02 BSC	
L	0.10	0.20	0.30	0.004	0.008	0.012
HE	1.50	1.60	1.70	0.059	0.062	0.066

#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and um are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC owns the rights to a number of patents, trademarks, ON Semiconductor and "U" are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

#### **PUBLICATION ORDERING INFORMATION**

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor Phone: 303–675–2175 or 800–344–3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910 Japan Customer Focus Center

Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative